

BRMJB42CQ

Rev.A Oct.-2023

/ Descriptions

TO-263 PNP

Silicon PNP transistor in a TO-263 Plastic Package.

/ Features

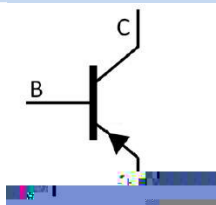
BRMJB41CQ AEC-Q101

Complement to BRMJB41CQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

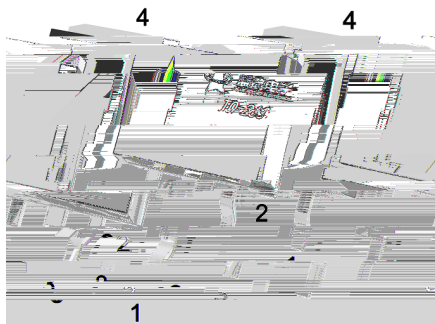
/ Applications

Medium power linear switching applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

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蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

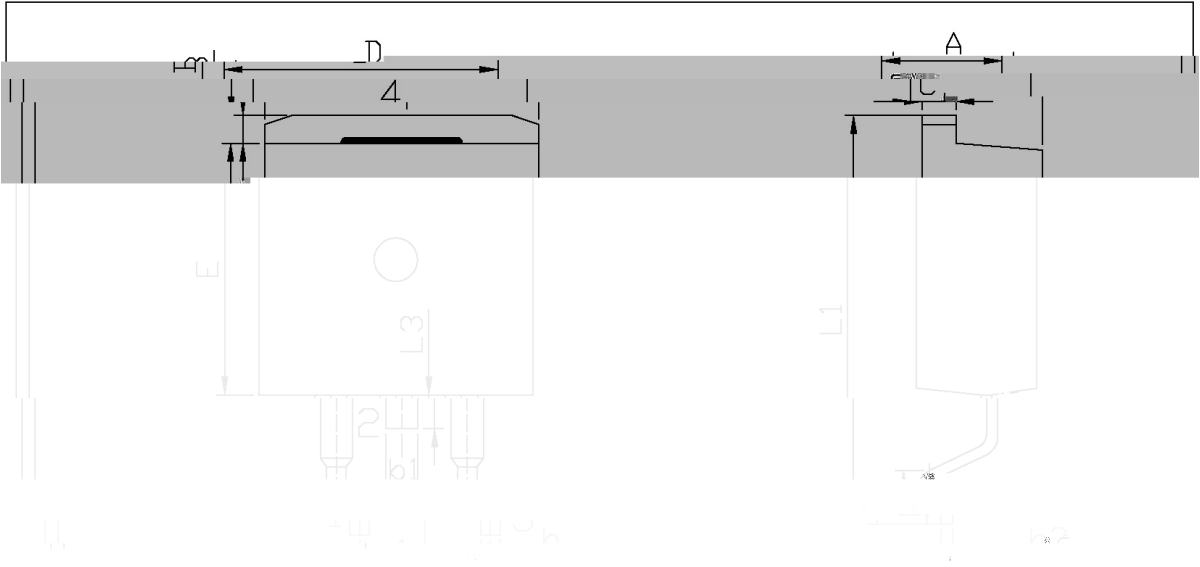
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-6.0	A
Peak Collector Current	I_{CP}	-10	A
Base Current - Continuous	I_B	-2.0	A
Power Dissipation	P_D	2.0	W
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	65	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-30\text{mA}$ $I_B=0$	-100			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-60\text{V}$ $I_B=0$			-0.7	mA

/ Electrical Characteristic Curve



/ Package Dimensions



Max	Min	Max	Min
9.40	4.30	4.70	9.00
2.74	1.00	1.40	2.24
0.88	0.80	0.80	0.80
5.00	16.00	b1	1.15
			1.35
			L1

() /

Note:

- 1

150 200

60 120sec;

1.Preheating:150~200 , Time:60~120sec.
- 2

255±5

5±0.5sec;

2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL